

# bq2204A

# X4 SRAM Nonvolatile Controller Unit

#### Features

- Power monitoring and switching for 3-volt battery-backup applications
- > Write-protect control
- 2-input decoder for control of up to 4 banks of SRAM
- > 3-volt primary cell inputs
- Less than 10ns chip-enable propagation delay
- ▶ 5% or 10% supply operation

#### **General Description**

The CMOS bq2204A SRAM Nonvolatile Controller Unit provides all necessary functions for converting up to four banks of standard CMOS SRAM into nonvolatile read/write memory.

A precision comparator monitors the 5V V<sub>CC</sub> input for an out-of-tolerance condition. When out-of-tolerance is detected, the four conditioned chip-enable outputs are forced inactive to write-protect up to four banks of SRAM.

During a power failure, the external SRAMs are switched from the VCC supply to one of two 3V backup supplies. On a subsequent power-up, the SRAMs are write-protected until a power-valid condition exists.

During power-valid operation, a two-input decoder transparently selects one of up to four banks of SRAM.

-	 	 	

**Pin Connections** 

#### VOUT 16 Vcc BC<sub>2</sub> 2 15 BC1 NC 14 CE 3 4 13 CECON1 вI 5 12 NC 6 11 THS 10 CECON4 NC 9 Vss 16-Pin Narrow DIP or SOIC PN220401 eng

#### Pin Names Vout Supply output BC1-BC2 3 volt primary backup cell inputs THS Threshold select input $\overline{CE}$ chip-enable active low input CE<sub>CON1</sub>-Conditioned chip-enable outputs **CE**CON4 A-B Decoder inputs NC No connect +5 volt supply input Vcc VSS Ground

#### **Functional Description**

Up to four banks of CMOS static RAM can be batterybacked using the V<sub>OUT</sub> and conditioned chip-enable output pins from the bq2204A. As V<sub>CC</sub> slews down during <u>a power failure</u>, the conditioned chip-enable outputs CE<sub>CON1</sub> through CE<sub>CON4</sub> are forced inactive independent of the chip-enable input CE.

This activity unconditionally write-protects the external SRAM as V<sub>CC</sub> falls below an out-of-tolerance threshold V<sub>PFD</sub>. V<sub>PFD</sub> is selected by the threshold select input pin, THS. If THS is tied to V<sub>SS</sub>, the power-fail detection occurs at 4.62V typical for 5% supply operation.

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If THS is tied to  $V_{CC}$ , power-fail detection occurs at 4.37V typical for 10% supply operation. The THS pin must be tied to VSS or  $V_{CC}$  for proper operation.

If a memory access is in process to any of the four external banks of SRAM during power-fail detection, that memory cycle continues to completion before the memory is writeprotected. If the memory cycle is not terminated within time tWPT, all four chip-enable outputs are unconditionally driven high, write-protecting the controlled SRAMs.

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As the supply continues to fall past VPFD, an internal switching device forces  $V_{OUT}$  to one of the two external backup energy sources. CECON1 through CECON4 are held high by the VOUT energy source.

During power-up, V<sub>OUT</sub> is switched back to the 5V supply as V<sub>CC</sub> rises above the backup cell input voltage sourcing V<sub>OUT</sub>. Outputs  $\overrightarrow{CE}_{CON1}$  through  $\overrightarrow{CE}_{CON4}$  are held inactive for time t<sub>CER</sub> (120ms maximum) after the power supply has reached V<sub>PFD</sub>, independent of the  $\overrightarrow{CE}$  input, to allow for processor stabilization.

During power-valid operation, the  $\overline{CE}$  input is passed through to one of the four  $\overline{CE}_{CON}$  outputs with a propagation delay of less than 10ns. The  $\overline{CE}$  input is output on one of the four  $\overline{CE}_{CON}$  output pins depending on the level of the decode inputs at A and B as shown in the Truth Table.

The A and B inputs are usually tied to high-order address pins so that a large nonvolatile memory can be designed using lower-density memory devices. Nonvolatility and decoding are achieved by hardware hookup as shown in Figure 1.

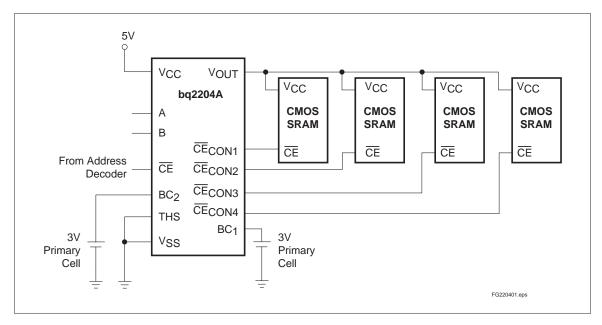


Figure 1. Hardware Hookup (5% Supply Operation)

#### Energy Cell Inputs—BC<sub>1</sub>, BC<sub>2</sub>

Two backup energy source inputs are provided on the bq2204A. The BC<sub>1</sub> and BC<sub>2</sub> inputs accept a 3V primary battery (non-rechargeable), typically some type of lithium chemistry. If no primary cell is to be used on either BC<sub>1</sub> or BC<sub>2</sub>, the unused input should be tied to V<sub>SS</sub>.

 $V_{CC}$  falling below  $V_{PFD}$  starts the comparison of  $BC_1$ and  $BC_2$ . The BC input comparison continues until  $V_{CC}$ rises above  $V_{SO}$ . Power to  $V_{OUT}$  begins with  $BC_1$  and switches to  $BC_2$  only when  $V_{BC1}$  is less than  $V_{BC2}$  minus  $V_{BSO}$ . The controller alternates to the higher BC voltage only when the difference between the BC input voltages is greater than  $V_{BSO}$ . Alternating the backup batteries allows one-at-a-time battery replacement and efficient use of both backup batteries.

To prevent batter<u>y</u> drain when there is no valid data to retain, V<sub>OUT</sub> and  $\overrightarrow{CE}_{CON1-4}$  are internally isolated from BC<sub>1</sub> and BC<sub>2</sub> by either of the following conditions:

- Initial connection of a battery to BC1 or BC2, or
- Presentation of an isolation signal on CE.

A valid isolation signal requires CE low as V<sub>CC</sub> crosses both V<sub>PFD</sub> and V<sub>SO</sub> during a power-down. See Figure 2. Between these two points in time, CE must be brought to the point of (0.48 to 0.52)\*V<sub>CC</sub> and held <u>for</u> at least 700ns. The isolation signal is invalid if CE exceeds 0.54\*V<sub>CC</sub> at any point between V<sub>CC</sub> crossing V<sub>PFD</sub> and V<sub>SO</sub>.

The appropriate battery is connected to  $V_{OUT}$  and  $\overline{CE}_{CON1-4}$  immediately on subsequent application and removal of  $V_{CC}.$ 

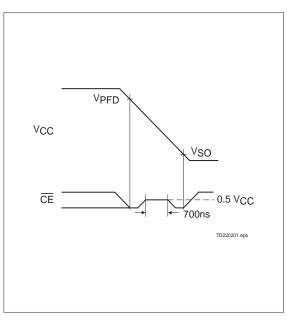


Figure 2. Battery Isolation Signal

	Input		Output						
CE	А	В	CE <sub>CON1</sub>	<b>CE</b> CON2	<b>CE</b> CON3	CE <sub>CON4</sub>			
Н	Х	Х	Н	Н	Н	Н			
L	L	L	L	Н	Н	Н			
L	Н	L	Н	L	Н	Н			
L	L	Н	Н	Н	L	Н			
L	Н	Н	Н	Н	Н	L			
<u>.</u>									

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**Truth Table** 

Symbol	Parameter	Value	Unit	Conditions
Vcc	DC voltage applied on V <sub>CC</sub> relative to V <sub>SS</sub>	-0.3 to +7.0	V	
VT	DC voltage applied on any pin excluding $V_{CC}$ relative to $V_{SS}$	-0.3 to +7.0	V	$V_T \!\leq\! V_{CC} + 0.3$
		0 to 70	°C	Commercial
TOPR	Operating temperature	0 to 70 °C -40 to +85 °C	°C	Industrial "N"
T <sub>STG</sub>	Storage temperature	-55 to +125	°C	
T <sub>BIAS</sub>	Temperature under bias	-40 to +85	°C	
TSOLDER	Soldering temperature	260	°C	For 10 seconds
IOUT	V <sub>OUT</sub> current	200	mA	

### **Absolute Maximum Ratings**

**Note:** Permanent device damage may occur if **Absolute Maximum Ratings** are exceeded. Functional operation should be limited to the Recommended DC Operating Conditions detailed in this data sheet. Exposure to conditions beyond the operational limits for extended periods of time may affect device reliability.

# **Recommended DC Operating Conditions (TA = TOPR)**

Symbol	Parameter	Minimum	Typical	Maximum	Unit	Notes
		4.75	5.0	5.5	V	THS = VSS
VCC	Supply voltage	4.50	5.0	5.5	V	THS = VCC
V <sub>SS</sub>	Supply voltage	0	0	0	V	
VIL	Input low voltage	-0.3	-	0.8	V	
VIH	Input high voltage	2.2	-	V <sub>CC</sub> + 0.3	V	
V <sub>BC1</sub> , V <sub>BC2</sub>	Backup cell voltage	2.0	-	4.0	V	V <sub>CC</sub> < V <sub>BC</sub>
THS	Threshold select	-0.3	-	V <sub>CC</sub> + 0.3	V	

**Note:** Typical values indicate operation at  $T_A = 25^{\circ}C$ ,  $V_{CC} = 5V$  or  $V_{BC}$ .

Symbol	Parameter	Minimum	Typical	Maximum	Unit	Conditions/Notes
ILI	Input leakage current	-	-	± 1	μΑ	VIN = VSS to VCC
VOH	Output high voltage	2.4	-	-	V	IOH = -2.0mA
VOHB	VOH, BC supply	V <sub>BC</sub> - 0.3	-	-	V	$V_{BC} > V_{CC}$ , $I_{OH} = -10 \mu A$
VOL	Output low voltage	-	-	0.4	V	$I_{OL} = 4.0 mA$
ICC	Operating supply current	-	3	6	mA	No load on outputs.
		4.55	4.62	4.75	V	THS = V <sub>SS</sub>
VPFD	Power-fail detect voltage	4.30	4.37	4.50	V	THS = V <sub>CC</sub>
VSO	Supply switch-over voltage	-	V <sub>BC</sub>	-	V	
ICCDR	Data-retention mode current	-	-	100	nA	V <sub>OUT</sub> data-retention current to additional memory not in- cluded.
	Active backup cell	-	VBC1	-	V	VBC1 > VBC2 + VBSO
VBC	voltage	-	VBC2	-	V	VBC2 > VBC1 + VBSO
VBSO	Battery switch-over voltage	0.25	0.4	0.6	V	
I <sub>OUT1</sub>	V <sub>OUT</sub> current	-	-	160	mA	V <sub>OUT</sub> > V <sub>CC</sub> - 0.3V
I <sub>OUT2</sub>	V <sub>OUT</sub> current	-	100	-	μΑ	$V_{OUT} > V_{BC} - 0.2V$

# DC Electrical Characteristics (TA = TOPR, VCC = 5V $\pm$ 10%)

**Note:** Typical values indicate operation at  $T_A = 25^{\circ}C$ ,  $V_{CC} = 5V$  or  $V_{BC}$ .

## Capacitance (T<sub>A</sub> = 25°C, F = 1MHz, V<sub>CC</sub> = 5.0V)

Symbol	Symbol Parameter		Typical	Maximum	Unit	Conditions
CIN	Input capacitance	-	-	8	pF	Input voltage = 0V
C <sub>OUT</sub>	Output capacitance	-	-	10	pF	Output voltage = 0V

**Note:** This parameter is sampled and not 100% tested.

## **AC Test Conditions**

Parameter	Test Conditions					
Input pulse levels	0V to 3.0V					
Input rise and fall times	5ns					
Input and output timing reference levels	1.5V (unless otherwise specified)					

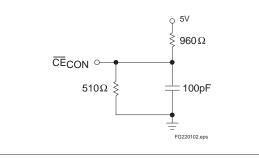


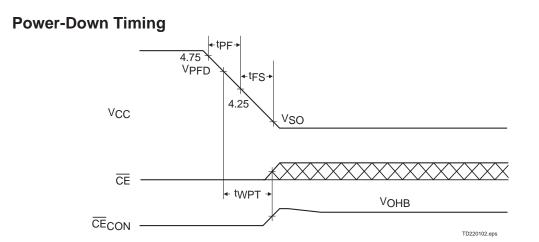
Figure 3. Output Load

# Power-Fail Control (TA = TOPR)

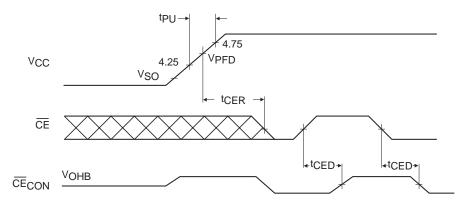
Symbol	Parameter	Minimum	Typical	Maximum	Unit	Notes
tPF	V <sub>CC</sub> slew, 4.75V to 4.25V	300	-	-	μs	
tFS	VCC slew, 4.25V to VSO	10	-	-	μs	
tPU	VCC slew, 4.25V to 4.75V	0	-	-	μs	
tCED	chip-enable propagation delay	-	7	10	ns	
tAS	A,B set up to $\overline{CE}$	0	-	-	ns	
t <sub>CER</sub>	chip-enable recovery	40	80	120	ms	Time during which SRAM is write-protected after $V_{CC}$ passes $V_{PFD}$ on power-up.
t <sub>WPT</sub>	Write-protect time	40	100	150	μs	Delay after V <sub>CC</sub> slews down past V <sub>PFD</sub> before SRAM is write-protected.

Note: Typical values indicate operation at  $T_A = 25^{\circ}C$ ,  $V_{CC} = 5V$ .

Caution: Negative undershoots below the absolute maximum rating of -0.3V in battery-backup mode may affect data integrity.

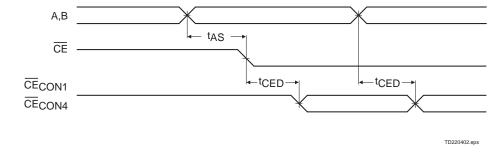


# **Power-Up Timing**



TD220103.eps

# **Address-Decode Timing**



# Data Sheet Revision History

Change No.	Page No.	Description of Change	Nature of Change
1	All	bq2204A replaces bq2204.	
1	1, 4–5	10% tolerance requires the THS pin to be tied to VCC, not VOUT.	
1	3	Energy cell input selection pro- cess alternates between BC <sub>1</sub> and BC <sub>2</sub> .	

**Note:** Change 1 = Dec. 1992 changes from Sept. 1991



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#### **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/ Ball Finish	MSL Peak Temp <sup>(3)</sup>	Samples (Requires Login)
BQ2204APN	ACTIVE	PDIP	Ν	16	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
BQ2204ASN	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	
BQ2204ASN-N	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	
BQ2204ASN-NG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	
BQ2204ASNG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	
BQ2204ASNTR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	
BQ2204ASNTRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

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<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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# PACKAGE MATERIALS INFORMATION

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#### TAPE AND REEL INFORMATION

#### REEL DIMENSIONS

TEXAS INSTRUMENTS





#### TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
BQ2204ASNTR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1

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# PACKAGE MATERIALS INFORMATION

14-Jul-2012



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
BQ2204ASNTR	SOIC	D	16	2500	367.0	367.0	38.0

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